

Product/Process Change Notification

N° 2020-121-A2

Dear customer,

please find attached our Infineon Technologies AG PCN:

Introduction of an additional plating subcon affecting dedicated products

Important information for your attention:

- Please respond to this PCN by indicating your decision on the approval form, sign it and return to your sales partner before 2021-07-28.
- Infineon aligns with the widely-recognized JEDEC STANDARD "JESD46", which stipulates: "Lack of acknowledgement of the PCN within 30 days constitutes acceptance of the change." Notwithstanding the aforesaid individual agreements shall prevail.

Your prompt reply will help Infineon to assure a smooth and well-executed transition. If Infineon does not hear from your side by the due date, we will assume your full acceptance to this proposed change and its implementation.

Your attention and response to this matter is greatly appreciated.







On 16 April 2020, Infineon acquired Cypress.

We are now in the process of merging and consolidating our tools and processes for PCN, Information Notes, Errata and Product Discontinuance. We ask for your patience in the meantime. For further details, please visit our website:

https://www.infineon.com/cms/en/about-infineon/company/cypress-acquisition/

Infineon Technologies AG

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Chairman of the Supervisory Board: Dr. Wolfgang Eder

Management Board: Dr. Reinhard Ploss (CEO), Dr. Helmut Gassel, Jochen Hanebeck, Constanze Hufenbecher, Dr. Sven Schneider

Registered Office: Neubiberg

Commercial Register: München HRB 126492



Product/Process Change Notification

N° 2020-121-A2

Products affected Please refer to attached affected product list 1_cip20121_A2

Detailed change information

Subject: Introduction of an additional plating subcon affecting dedicated products

Reason/Motivation: To ensure secure supply

PROCESS - ASSEMBLY: Move all or parts of production to a different assembly site.

Plating subcon: Ishizaki (SII) Sdn. Bhd, Malaysia

Plating subcon: Ishizaki (SII) Sdn. Bhd, Malaysia

or

Syntronixs Asia (SA) Sdn. Bhd, Malaysia

Product identificationTraceability is assured via internal lot number.

Anticipated impact of change

impact on quality and reliability.

No impact on fit, form and function

DeQuMa-ID(s): SEM-PA-18

Attachments

1_cip20121_A2 affected product list
2_cip20121_A2 qualification report
3_cip20121_A2 customer information package

Time schedule

Final qualification report	available
First samples available	on request
Intended start of delivery [1]	2021-07-31
Last order date (LOD) [2]	2022-01-31
Last delivery date (LDD) [3]	2022-07-31

^[1] provided date or earlier after customer approval

^[2] Last time buy volume to be placed latest until LOD

^[3] Delivery of new product can be earlier (see Intended start of delivery) and depends on approval



Product/Process Change Notification

N° 2020-121-A2

If you have any questions, please do not hesitate to contact your local sales office.

Infineon Technologies AG	Component Qualification Test Plan for Packaged Integrated Circuits	ATV QM
	according to AEC Q100 Rev. H	

Project	TDSO Subcon Plating at Syntronixs Asia (SA)	Date: 2021-06-15
Part for family qualification	TLE5014C16D,TLE4998C8D, TLE5309D E1211, TLE4999C8	Department: IFAG ATV QM SC MSS
Chips for family qualification	M5014A, M4998L, M5009A (top) / M5109A (bottom), M4991A	Provided by: L. Langkopf, S. Vasquez-Borucki, M. Schindler, F. Durrani
Device family	Linear Hall and Angle Sensor product families	
Qualification no.	Q20ETS05	Reviewed by: J. Specht, F. Schröppel

Part Operating Temperature Grade 1:

-40°C to 125°C ambient Operating Temperature Range

	Part	Chip	Chip size [mm²]	Wafer diameter [mm]	Wafer fab	Wafer technology	Package	Assembly line
Part to be Qualified	TLE5014C16D	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Qualified	TLE4998C8D	M4998L	2.90 x 1.90	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Qualified	TLE5309D E1211	M5009A (top) M5109A (bottom)	1.40 x 1.40 1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR C9FLRN_AMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Qualified	TLE4999C8	M4991A	1.46 x 1.61	200	Infineon Technologies Dresden, Germany	SPT9_S8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014S16D	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014P16D	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014C16D E0015	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014SP16D E0002	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014C16	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia

IFAG ATV QM SC restricted 1/8 QTR_Q100H_TDSO_Plating_Subcon_Syntronixs_PCN

Infineon Technologies AG		Component Qu according to Al		Plan for Pa	ckaged Integrated Circuits			ATV QM
Part to be Released	TLE5014S16	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014P16	M5014A	1.90 x 1.60	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014SP16 E0001	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5014SP16 E0002	M5014A	1.90 x 1.60	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	SPT9_xMR8	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4997A8D	M4997K	2.95 x 2.20	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4997A8D	M4997M	2.95 x 2.20	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4997A8D E0300	M4997K	2.95 x 2.20	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4997A8D E0300	M4997M	2.95 x 2.20	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4997A8	M4997K	2.95 x 2.20	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4997A8	M4997M	2.95 x 2.20	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998C8D	M4998B	2.90 x 1.90	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998P8D	M4998K	2.90 x 1.90	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998P8D	M4998A	2.90 x 1.90	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998S8D	M4998L	2.90 x 1.90	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998S8D	M4998B	2.90 x 1.90	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-2	Infineon Technologies Melaka, Malaysia

IFAG ATV QM SC restricted 2 / 8 QTR_Q100H_TDSO_Plating_Subcon_Syntronixs_PCN

Infineon Technologies AG	3	Component Qua		Plan for Pa	ckaged Integrated Circuits			ATV QM
Part to be Released	TLE4998C8	M4998L	2.90 x 1.90	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998C8	M4998B	2.90 x 1.90	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998P8	M4998K	2.90 x 1.90	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998P8	M4998A	2.90 x 1.90	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998S8	M4998L	2.90 x 1.90	200	Infineon Technologies Kulim Sdn Bhd	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE4998S8	M4998B	2.90 x 1.90	200	Infineon Technologies Regensburg, Germany	B6CAS_8	PG-TDSO-8-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16D E1200	M5009A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16D E1210	M5009A	1.40 x 1.40	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16D E2200	M5009A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg,	C9FLRN_GMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16D E2210	M5009A	1.40 x 1.40	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16 E1200	M5009A	1.40 x 1.40	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16 E2200	M5009A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg,	C9FLRN_GMR	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5009A16 E2210	M5009A	1.40 x 1.40	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg,	C9FLRN_GMR	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5012BD E1200	M5012B	2.00 x 2.00	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
Part to be Released	TLE5012BD E9200	M5012B	2.00 x 2.00	200	Germany Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia

IFAG ATV QM SC restricted 3/8 QTR_Q100H_TDSO_Plating_Subcon_Syntronixs_PCN

Inf	ineon Technologies AG	ATV QM							
	Part to be Released	TLE5309D E2211	M5009A (top) M5109A (bottom)	1.40 x 1.40 1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR C9FLRN_AMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
	Part to be Released	TLE5309D E5201	M5009A (top) M5109A (bottom)	1.40 x 1.40 1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_GMR C9FLRN_AMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
	Part to be Released	TLE5109A16D E1210	M5109A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_AMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
	Part to be Released	TLE5109A16D E2210	M5109A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_AMR	PG-TDSO-16-2	Infineon Technologies Melaka, Malaysia
	Part to be Released	TLE5109A16 E1210	M5109A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg, Germany	C9FLRN_AMR	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia
	Part to be Released	TLE5109A16 E2210	M5109A	1.40 x 1.40	200	Infineon Technologies Dresden, Germany & Infineon Technologies Regensburg,	C9FLRN_AMR	PG-TDSO-16-1	Infineon Technologies Melaka, Malaysia

Result: Qualification passed

IFAG ATV QM SC restricted 4/8 QTR_Q100H_TDSO_Plating_Subcon_Syntronixs_PCN

Infineo	ineon Technologies AG Component Qualification Test Plan for Packaged Integrated Circuits according to AEC Q100 Rev. H													ATV QN	
	Project Device no. for family qualification Chip no. for family qualification Device family Qualification no.	TDSO Subcon Plating at Syn TLE5014C16D,TLE4998C8D, M5014A, M4998L, M5009A (to Linear Hall and Angle Senso Q20ETS05	TLE5309D pp) / M5109	E1211, TLE4 A (bottom),					Date: Department: Provided by: Reviewed by:	2021-06-15 IFAG ATV QM SC MSS L. Langkopf, S. Vasquez-Borucki, M. Schindler, F. Durrani J. Specht, F. Schröppel					
	Qualification no.	Q20E1303												Reviewed by.	3. эреспі, г. эспгоррег
TEST#	STRESS TEST according AEC Q100 Rev.H	Test conditions	# LOTS	Sample Size	Duration		be Qualified ails/S.S.		be Qualified ails/S.S.		o be Qualified Fails/S.S.		o be Qualified Fails/S.S.		Remarks
							5014C16D M5014A		E4998C8D M4998L	M5	TLE5309D E1211 M5009A (top) M5109A (bottom) TLE4999C8 M4991A				
						Fail	Devices	Fail	Devices	Fail	Devices	Fail	Devices		
	Solder Preconditioning; MSL3/ 260°C J-STD-020; JESD22-A113	moisture soak 192h 30°C/60%r.h.	3	231 77	-	С	231	C	231	C	231	0	77	Preconditioning	before tests # A2, A3, A4
A2	Temperature Humidity Bias	85°C/85%r.h. Vs= 3.3V	3	77	500h 1000h		77 77		77 77) 77) 77	-	-	Acc. to Table 2A WBP of 3 lots P	, AEC Q100 Rev.H ASSED
A3	Unbiased HAST	110°C / 85% r.h.	4	77	264h	C	77	(77	C	77	0	77	Acc. to Table 2A	, AEC Q100 Rev.H
A4	Temperature Cycling	-55°C / +150°C	3	77	500c 1000c		77 77		77 77	-) 77) 77	-	-	Acc. to Table 2A	, AEC Q100 Rev.H
A5	Power Temperature Cycling		-	-	-	-	-	-	-	-	-	-	-	Not applicable: [Device is rated < 1W and ΔT_J < $40^{\circ}C$
A6	High Temperature Storage Life	Ta = +150°C	4	77	500h 1000 h	0	77 77		77 77) 77) 77		77 77		
B1	High Temperature Operating Life		-	-	-	-	-	-	-	-	-	-	-	Not applicable: F	HTOL is not requested according to AEC
B2	Early Life Failure Rate		-	-	-	-	-	-	-	-	-	-	-	Not applicable: Not applicable	New plating supplier is not expected to affectoroducts in TDSO package.
В3	NVM Endurance, Data Retention		-	-	-	-	-	-	-	-	-	-	-	Not applicable: Not applicable	NVM Endurance test not related to plating

IFAG ATV QM SC restricted 5 / 8

Infineo	n Technologies AG		Component Qualification Test Plan for Packaged Integrated Circuits according to AEC Q100 Rev. H														
	Project Device no. for family qualification Chip no. for family qualification Device family Qualification no.	TDSO Subcon Plating at Syntro TLE5014C16D,TLE4998C8D, TLI M5014A, M4998L, M5009A (top) Linear Hall and Angle Sensor pr Q20ETS05	E5309D / M5109	E1211, TLE4 A (bottom),			Date: Department: Provided by: Reviewed by:	2021-06-15 IFAG ATV QM SC MSS L. Langkopf, S. Vasquez-Borucki, M. Schindler, F. Durrani J. Specht, F. Schröppel									
TEST#	STRESS TEST according AEC Q100 Rev.H	Test conditions	# LOTS	Sample Size	Duration		be Qualified fails/S.S.		be Qualified ails/S.S.		o be Qualified Fails/S.S.		o be Qualified Fails/S.S.		Remarks		
							5014C16D M5014A		E4998C8D M4998L	M5	TLE5309D E1211 M5009A (top) M5109A (bottom)		M5009A (top)		_E4999C8 M4991A		
						Fail	Devices	Fail	Devices	Fail	Devices	Fail	Devices				
C1	Wire Bond Shear		3	10 / 30 bonds		C	30	C	30	(0 30	-	-	AEC Q100-001,	AEC Q003		
C2	Wire Bond Pull		3	10 / 30 bonds	-	C	30	C	30	(0 30	-	-	AEC Q003			
С3	Solderability	PC: 8 hours ± 15mins, Steam age (93°C ± 3°C / 100 % r.h) Solder Type: SnAgCu Test: Temp: 245°C±5°C, Dip Time: 5 ±0.5sec	3	15	-	C) 15	C	15	(0 15	-	-	JEDEC J-STD-002 Additional conditions: Solderability Test Wetting / Dewetting Dip & Look Pre-Test and Post Test 15pcs / 3 Test Conditions / 3 Lots			
C4	Physical Dimensions		-	-	-	-	-	-	-	-	-	-	-	Monitoring by Bl	E, reported in PPAP		
C5	Solder Ball Shear		-	-	-	-	-	-	-	-	-	-	-	Not applicable: Not applicable	No Solder Ball Surface Mount Packaged		
C6	Lead Integrity		-	-	-	-	-	-	-	-	-	-	-	Not applicable: N	No through-hole device		
D1	Electromigration		-		-	-	-	-	-	-	-	-	-	Not applicable: F	Part of Technology Qualification		
	Time Dependent Dielectric Breakdown		-	-	-	-	-	-	-	-	-	-	-	Not applicable: F	Part of Technology Qualification		
D3	Hot Carrier Injection		-	-	-	-	-	-	-	-	-	-	-	Not applicable: F	Part of Technology Qualification		
D4	Negative Bias Temperature Instability		-	-	-	-	-	-	-	-	-	-	-	Not applicable: F	Part of Technology Qualification		
D6	Stress Migration		-	-	-	-	-	-	-	-	-	-	-	Not applicable: F	Part of Technology Qualification		

6/8

Infineo	n Technologies AG		Component Qualification Test Plan for Packaged Integrated Circuits according to AEC Q100 Rev. H													
	Project Device no. for family qualification Chip no. for family qualification Device family Qualification no.	for family qualification M5014A, M4998L, M5009A (top) / M5109A (bottom), M4991A amily Linear Hall and Angle Sensor product families												Date: Department: Provided by: Reviewed by:	2021-06-15 IFAG ATV QM SC MSS L. Langkopf, S. Vasquez-Borucki, M. Schindler, F. Durrani J. Specht, F. Schröppel	
TEST#	STRESS TEST according AEC Q100 Rev.H	Test conditions	# LOTS	Sample Size	Duration		be Qualified ails/S.S.		be Qualified fails/S.S.		o be Qualified Fails/S.S.	Part to be Qualified Fails/S.S.			Remarks	
							5014C16D //5014A		E4998C8D M4998L	M5	5309D E1211 5009A (top) 09A (bottom)		LE4999C8 M4991A			
						Fail	Devices	Fail	Devices	Fail	Devices	Fail	Devices			
E1	Pre- and Post-Stress	Test to spec	4	all	-	0	all	0	all		0 all	(all	Post-Stress: Re	er to individual test	
	Electrostatic Discharge Human Body Model ANSI/ESDA/JEDEC JS-001		-	3/voltage	-	-	-	-	-	-	-	-	-	Not applicable: Not applicable	No further failure mechanisms are expected lischarge types.	
D1	Electromigration		-	-	-	-	-	-	-	-	-	-	-	Not applicable: F	Part of Technology Qualification	
	Electrostatic Discharge Charged Device Model JESD22-C101	500V (all pins) 750 V (corner pins)		3/voltage	-	-	-	-	-	-	-	-	-	Not applicable: Not applicable	No further failure mechanisms are expected discharge types.	
E4	Latch-Up JESD 78	Ta = +150°C Vs = 5.5 V Itrigger = 150mA	-	6	-	-	-	-	-	-	-	-	-	Not applicable: Not applicable	No LU failure mechanisms are expected with r project.	
E5	Electrical Distributions AEC Q100-009	-40°C, 25°C, 125°C	4	30	-	0	30	O	30		0 30	(30			
E12	Lead (Pb) Free		3	-	-	0	see remarks	d	see remarks		0 see remarks	-	-	AEC-Q005-Rev report available.	A: Solderability (refer to C3). Whisker test	
E12a	Lead (Pb) Free: Solderability		-	-	-	-	-	-	-	-	-	-	-	Referenced to #	C3: Solderability	
E12b	Lead (Pb) Free: Resistance to Solder Heat		-	-	-	-	-	-	-	-	-	-	-	recommended to by bottom-side v	AEC Q005 states: It is strongly nat active SMT components not be attached wave solder processes. Full Body Immersion be performed if requested by the user.	

IFAG ATV QM SC restricted 7 / 8

Infineon Technologies AG Component Qualification Test Plan for Packaged Integrated Circuits according to AEC Q100 Rev. H													AT\								
	Project Device no. for family qualification Chip no. for family qualification Device family Qualification no.	b. for family qualification M5014A, M4998L, M5009A (top) / M5109A (bottom), M4991A Linear Hall and Angle Sensor product families											Date: Department: Provided by: Reviewed by:	2021-06-15 IFAG ATV QM SC MSS L. Langkopf, S. Vasquez-Borucki Schindler, F. Durrani J. Specht, F. Schröppel							
TEST#	STRESS TEST according AEC Q100 Rev.H	Test conditions	# LOTS	Sample Size	Duration		be Qualified fails/S.S.		o be Qualified Fails/S.S.		to be Qualified Fails/S.S.		o be Qualified Fails/S.S.		Remarks						
							5014C16D M5014A		E4998C8D M4998L	M	TLE5309D E1211 M5009A (top) M5109A (bottom)		M5009A (top)		M5009A (top)		M5009A (top)		LE4999C8 M4991A		
						Fail	Devices	Fail	Devices	Fail	Devices	Fail	Devices								
E12c	Lead (Pb) Free: Moisture Sensitivity		-	-	-	-	-	-	-	-	-	-	-	Referenced to # /	11: Preconditioning						
E12d	Lead (Pb) Free: Sn whisker testing		-	-	-	-	-	-	-	-	-	-	-	Refer to Whisker Test Report							
F1	Process Average Testing		-	-	-	-	-	-	-	-	-	-	-	Implemented in p	roduction						
F2	Statistical Bin/Yield Analysis		-	-	-	-	-	-	-	-	-	-	-	Implemented in p	roduction						
G1-G4	Hermetic Package Tests		-	-	-	-	-	-	-	-	-	-	-	Not applicable: N	o hermetic package device						
G5	Package Drop		-	-	-	-	-	-	-	-	-	-	-	Not applicable: N	o hermetic package device						
G6	Lid Torque		-	-	-	-	-	-	-	-	-	-	-	Not applicable: N	o hermetic package device						
G7	Die Shear		-	-	-	-	-	-	-	-	-	-	-	Not applicable: N	o hermetic package device						
G8	Internal Water Vapor		-	-	-	-	-	-	-	-	-	-	-	Not applicable: N	o hermetic package device						
	Supplier: Infineon Technologies AG									•				-							

IFAG ATV QM SC restricted 8 / 8

Infineon Technologies AG	Component Qualification Test Plan for Packaged Integrated Circuits	ATV QM
	according to AEC Q100 Rev. H	

Project	Torque sensor, TLE4999i	Date: 2021-06-15
Part for family qualification	TLE4999i	Department: ATV QM ATV SC MSS
Chip for family qualification	M4999	Provided by: V. Güngerich
Device family	Linear Hall	
Qualification no.	Q20ETS05	Reviewed by: F. Durrani

Part Operating Temperature Grade 0

-40°C to 150°C

Family qualification (generic data) with structual similar (representative) types

	Part	Chip	Chip size [mm²]	Wafer diameter [mm]	Wafer fab	Wafer technology	Package	Assembly line
Part to be Qualified	TLE4999i	M4999	1.00 x 2.20	200	Infineon Technologies AG, Dresden / Germany	SPT9_S	PG-SSO-3-12	Infineon Technologies Snd Bhd, Melaka / Malaysia

Result: Qualification passed

Project Torque sensor, TLE4999i Date: 2021-06-15 Device no. for family qualification Chip no. for family qualification TLE4999i Department: ATV QM ATV SC MSS

M4999 Provided by: V. Güngerich Device family Linear Hall

Reviewed by: F. Durrani Qualification no. **Q20ETS05**

TEST#	STRESS TEST	Test conditions	# Q- LOTS	Sample Size	Duration		ified parts ls/ parts)				fied parts s/ parts)	Remarks
						TL	.E4999i	TL	.E4999i	TL	E4999i	
						Fails	Devices	Fails	Devices	Fails	Devices	
A1	Dip soldering	Ta = 260°C, 10 sec, 1x	1	480		C	308	0	308	0	308	DIP soldering JESD22-B102B
A2	Temperature Humidity Biased	Vs=5,5 V Ta = 85°C/85%r.h.	3	77	500h 1000h		77 77		77 77		77 77	acc. to Table 2, AEC Q100 Rev.H
А3	Unbiased Hast	Ta = 110°C / 85% r.h.	3	77	264h	C	77	0	77	0	77	acc. to Table 2, AEC Q100 Rev.H
A4	Temperature Cycling (Air to Air)	Ta = -55°C / +150°C	3	77	1000c 2000c		77 77		77 77	0	77 77	acc. to Table 2, AEC Q100 Rev.H
A6	High Temperature Storage Life (HTSL)	Ta = +175°C	3	77	500h 1000h 1500h	O	77 77 77	0	77 77 77	0	77 77 77	acc. to Table 2, AEC Q100 Rev.H
B3	High Temperature Operating Life (HTOL) NVM Endurance, Data Retention, & Operational Life EDR 50 cycles @ 85°C Functional programming	Tjmax = +175°C Vdd = 7,0 V	3	77	500h 1000h 1500h 3000h	-	-	-	-	-	-	Not applicable: HTOL is not requested according to AEC Q100
	High Temperature Data Retention (HTDR) EDR 50 cycles @ 85°C Checkerboard	Ta = +175°C	3	77	500h 1000h 1500h	-	-	-	-	-	-	Not applicable: NVM Endurance test not related to plating process change.
В3	Low Temperature Data Retention (LTDR) EDR 50 cycles @ 55°C Checkerboard	Ta = 25°C	3	77	500h 1000h 1500h	-	-	-	-	-	-	Not applicable: NVM Endurance test not related to plating process change.

Project Torque sensor, TLE4999i Device no. for family qualification Chip no. for family qualification

M4999 Device family Linear Hall

Qualification no.

TLE4999i

Q20ETS05

Date: 2021-06-15

Department: ATV QM ATV SC MSS

Provided by: V. Güngerich

Reviewed by: F. Durrani

TEST#	STRESS TEST	Test conditions	# Q- LOTS	Sample Size	Duration		ified parts s/ parts)	Qualified parts (fails/ parts)		Qualified parts (fails/ parts)		Remarks
						TL	.E4999i	TL	.E4999i	TLE4999i		
						Fails	Devices	Fails	Devices	Fails	Devices	
							1					
C1	Wire Bond Shear		3	5		0	5	0	5	0	5	acc. to Table 2, AEC Q100 Rev.H
C2	Wire Bond Pull		3	5		0	5	0	5	0	5	acc. to Table 2, AEC Q100 Rev. H MIL STD883, Method 2011
C3	Solderability		3	15		0	15	0	15	0	15	JESD22-B102B
C4	Physical Dimensions		3	10		0	10	0	10	0	10	JEDEC JESD22-B100
C6	Lead Integrity		3	10		-	-	-	-	-	-	Not applicable: Lead integrity test not related to plating process change.
D1	Electromigration		3	20/ condition	variable	-	-	-	-	-	-	Not applicable: part of Technology Qualification
D2	Time Depending Dieelectric Breakdown		3	30/ condition	variable	-	-	-	-	-	-	Not applicable: part of Technology Qualification
D3	Hot Carrier Injection		3	15/ condition	variable	-	-	-	-	-	-	Not applicable: part of Technology Qualification
D4	Negative Bias Temperature Instability		3	15/ condition	variable	-	-	-	-	-	-	Not applicable: part of Technology Qualification
D5	Stress Migration		3	50/ condition	2000 h	-	-	-	-	-	-	Not applicable: part of Technology Qualification

Project Torque sensor, TLE4999i

Linear Hall

Device family

Date: 2021-06-15 Device no. for family qualification Chip no. for family qualification TLE4999i Department: ATV QM ATV SC MSS M4999 Provided by: V. Güngerich

Reviewed by: F. Durrani Qualification no. **Q20ETS05**

TEST#	STRESS TEST	Test conditions	# Q- LOTS	Sample Size	Duration		ified parts ls/ parts)	Qualified parts (fails/ parts)		Qualified parts (fails/ parts)		Remarks
						TL	.E4999i	TL	.E4999i	TLE4999i		
						Fails	Devices	Fails	Devices	Fails	Devices	
E1	Pre- and Post-Stress	Test to spec	3	all	-	0	all	0	all	0	all	Post-Stress: refer to individual test
	Electrostatic Discharge Human Body Model	500 V 1000 V 2000 V 3000 V 4000 V 5000 V	3	3/voltage		+	-	-	-	-	-	Not applicable: No further failure mechanisms are expected with ESD HBM discharge types.
	Electrostatic Discharge Charge Device Model	250 V 500 V 750 V 1000V 1250 V 1500 V	3	3/voltage		-	-	-	-	-	-	Not applicable: No further failure mechanisms are expected with ESD CDM discharge types.
E4	Latch-Up		3	6		-	-	-	-	-	-	Not applicable: No LU failure mechanisms are expected with package transfer project.
E5	Electrical Distributions	-40°C, 25°C, 150°C	3	30		0	30	0	30	0	30	acc. to Table 2, AEC Q100 Rev.H
E12	Lead (Pb) Free		3	-	-	0	see remarks	0	see remarks	0	see remarks	AEC-Q005-Rev A: Solderability (refer to C3). Whisker test report are available.
E12a	Lead (Pb) Free: Solderability		-	-	-	-	-	-	-	-	-	referenced to # C3: Solderability
E12b	Lead (Pb) Free: Resistance to Solder Heat		-	-		-	-	-	-	-	-	referenced to # A1: DIP Soldering
E12c	Lead (Pb) Free: Moisture Sensitivity		n.a.	-	1	,	-	-	-	,	-	Through hole package
E12d	Lead (Pb) Free: Sn whisker testing		-	-	-	-	-	-	-	-	-	refer to Whisker Test Report

Infineon Technologies AG	Component Qualification Test Plan	ATV QM
	for Packaged Integrated Circuits according to AEC Q100 Rev.H	

Torque sensor, TLE4999i Project Device no. for family qualification Chip no. for family qualification TLE4999i

Device family Qualification no. M4999 Linear Hall Date: 2021-06-15

Department: ATV QM ATV SC MSS

Provided by: V. Güngerich

Reviewed by: F. Durrani **Q20ETS05**

TEST#	STRESS TEST	Test conditions	# Q- LOTS	Sample Size	Duration		Qualified parts (fails/ parts)		Qualified parts (fails/ parts)		fied parts s/ parts)	Remarks
						TL	E4999i	TLE4999i		TLE4999i		
						Fails	Devices	Fails	Devices	Fails	Devices	
F1	Process Average Testing		-	-	-		-	-	-		-	Implemented in production
F2	Statistical Bin/Yield Analysis		-	-	-	-	-	-	-	-	-	Implemented in production
G1-G4	Hermetic Package Tests		-	-	-	1	-	-	-	-	-	Not applicable: No hermetic package device
G5	Package Drop		-	-	-	1	-	-	-	-	-	Not applicable: No hermetic package device
G6	Lid Torque		-	-	-	-	-	-	-	-	-	Not applicable: No hermetic package device
G7	Die Shear		-	-	-	-	-	-	-	-	-	Not applicable: No hermetic package device
G8	Internal Water Vapor		-	-	-	-	-	-	-	-	-	Not applicable: No hermetic package device

Introduction of an additional plating subcon affecting dedicated products

Customer Information Package PCN 2020-121-A2





1	Motivation of the change	3
2	Change overview	5
3	5M+1E Evaluation and comparison	8
4	Environment comparison (environment)	11
5	Operator training (man)	14
6	Equipment comparison (machine)	16
7	Structure comparison table & materials (material)	18
8	Process flow comparison (method)	20



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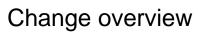
Motivation of the change



- To maintain secure supply of Infineon products to our customers, Infineon decided to add plating subcontractor Syntronixs Asia Sdn Bhd (SA), an ISO 9001 certified company, located in Malacca, Malaysia close to the Infineon Technology manufacturing plant for additional products.
- For more than 10 years Infineon has a relationship with SA as plating subcontractor for different packages
- SA will perform deflashing and plating processes for Infineon products. There are no significant differences in terms of equipment, process and material used compared to existing plating subcons. Qualification on reference products will ensure that Infineon's stringent quality targets are met and first positive readout results are available already.



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Description	Old	New
Plating subcon	Ishizaki (SII) Sdn. Bhd, Malaysia	Ishizaki (SII) Sdn. Bhd, Malaysia or Syntronixs Asia (SA) Sdn. Bhd, Malaysia

Syntronixs Asia (SA): introduction



- > Started in mid 2007 & mass production commenced in Jan 2009, high volume production since 5 years for similar packages (e.g. DSO-8, DSO-14, SSOP24, LQFP)
- Strategically located in Batu Berendam Free Industrial Zone. Melaka, close to our fab
- Specialize in Tin (Sn) and Copper (Cu) plating, capable depending on customer requirements
- Utilizing Meco plating equipment 17 plating lines in operation
- Consist of experience crew (process and equipment) to ensure production stability and speed in NPI (new product introduction)
- Available space options for future expansion possibilities to support customers' volume expansion



Advanced Electro-Plating for Electronics and Semiconductor Industry



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5M+1E Evaluation method



- The 5M+1E is a method used to analyze causes and consequences.
- The method is used to identify and prevent potential factors causing problems in production processes and having an overall effect.
- > Causes are grouped into 6 major categories to identify and classify these sources of variation
 - 5M:
 - Man, Machine, Material, Method, Measurement
 - 1E:
 - Environment





No	Items -	Comparison		Concerning point	Check Items	Check result	Evidence
INO		Existing	After PCN	Concerning point	Check items	Check result	Evidence
1	Environment	Ishizaki (SII), Melaka	Syntronixs Asia (SA), Melaka	Reduced solderability and increased delamination due to environment differences	Process comparison and qualification	Process parameter and qualification results are comparable	N/A
2	Man	Ishizaki (SII), Melaka	Syntronixs Asia (SA), Melaka	Different operation due to lack of operator training	Operator training	Similar level of training is implemented in both locations	Certification
3		Chemical DIP High Pressure Water Jet Sn Plating	Chemical DIP High Pressure Water Jet Sn Plating		Process comparison and qualification	1 '	Process comparison Qualification results Machine comparison table
4	Material	Plating chemistry	Plating chemistry		Process comparison and qualification	qualification results are	Process comparison Qualification results Material comparison table
5	Method	Chemical DIP Sn Plating	Chemical DIP Sn Plating		Process comparison and qualification	Process parameter and qualification results are comparable	Process comparison Qualification results
6	Measurement	N/A	N/A	N/A	N/A	N/A	N/A



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Syntronixs Asia Sdn. Bhd Plating and Annealing Equipment

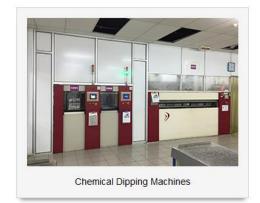




Meco EDF+EPL 2400S Straight Line









2021-06-09

Syntronixs Asia Sdn. Bhd Quality Control Equipment











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Man:

Operator training











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Machine:

Equipment comparison for plating



No	Breakdown of Tool Delta	Ishizaki (SII)	Syntronixs Asia (SA)	Assessment
1	Chemical dip	Custom Made Semi-Auto CD	Steda 1500	Comparable Process Performance
2	Water jet	MECO in-line with Sn plating	Steda & MECO	Comparable Process Performance
3	Sn plating	MECO	MECO	Comparable Process Performance
4	Annealing	Espec	Blue M / Enviro / Espec	Comparable Process Performance

> Comparable Process Performance for all different equipment



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Materials and suppliers used at Ishizaki (SII) and Syntronixs Asia (SA) are comparable

Items	Ishizaki (SII)	Syntronixs Asia (SA)
Chemical dip chemistry	Supplier A Material: A1	Supplier B Material: A2
Plating bath	Supplier C Material: C1	Supplier C Material: C2
Electro-degrease chemistry	Supplier D Material: D1	Supplier D Material: D2
Cu descaler chemistry	Supplier E Material: E1	Supplier F Material: E1
Pre dip chemistry	Supplier G Material: G1	Supplier H Material: G1
Sn plating chemistry	Supplier I Material: I1*	Supplier I Material: I2*

^{*} material used for the plating process has a slight difference but leading to same pure Sn plating

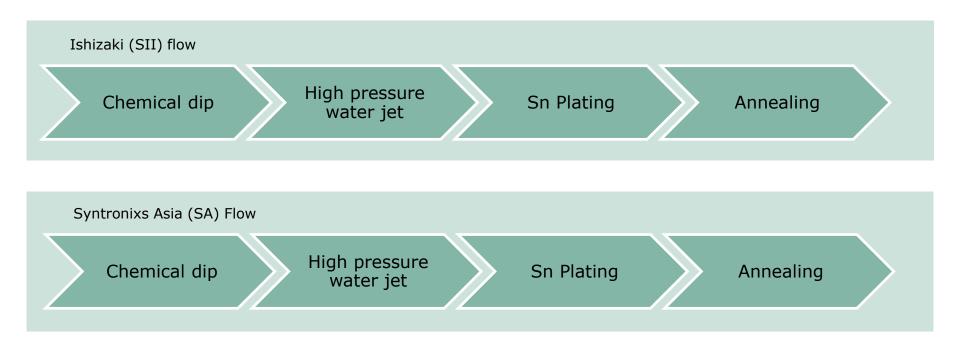


8	Process flow comparison (method)	20
7	Structure comparison table & materials (material)	18
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Process flow comparison



> Process flow used at Ishizaki (SII) and Syntronixs Asia (SA) are comparable





Part of your life. Part of tomorrow.